



Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	2.8Ω @ V _{GS} = 10V	350mA
307	3.8Ω @ V _{GS} = 5V	300mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

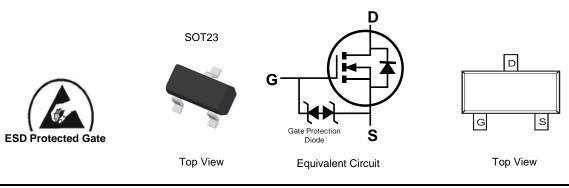
N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D8L-7	SOT23	3000/Tape & Reel
DMN63D8L-13	SOT23	10000/Tape & Reel

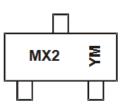
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} MX2 = Product Type Marking Code \\ YM \ or \ VM = Date Code Marking \\ Y \ or \ V = Year (ex: B = 2014) \\ M = Month (ex: 9 = September) \end{array}$

Date Code Key

Date Code R	ley											
Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н	I	J	K	L	М
						-		-	_	_		-
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	2	4	5	6	7	0	0	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
	Steady State	T _A = +25°C T _A = +70°C	ID	350 280	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	T _A = +25°C T _A = +70°C	ID	400 310	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			IDM	1.2	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	359	°C/W
Total Power Dissipation (Note 6)		PD	520	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	243	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			71			
Drain-Source Breakdown Voltage	BV _{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS	_		1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_		±10.0	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.8		1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
				2.8		$V_{GS} = 10.0V, I_D = 250mA$
			—	3.8		$V_{GS} = 5.0V, I_D = 250mA$
Static Drain-Source On-Resistance	R _{DS(ON)}			4.2	Ω	$V_{GS} = 4.5V, I_D = 250mA$
				4.5		$V_{GS} = 4.0V, I_D = 250mA$
				13		$V_{GS} = 2.5V, I_D = 10mA$
Forward Transconductance	g fs	80	_	_	mS	V _{DS} = 10V, I _D = 0.115A
Diode Forward Voltage	V _{SD}		0.8	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		23.2	—		
Output Capacitance	Coss	_	3.0	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	Crss		2.2			
Gate Resistance	R _G	_	79.9	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge V _{GS} = 10V	Qg	_	0.9	_		
Total Gate Charge V _{GS} = 4.5V	Qg	_	0.4	_	nC	$V_{GS} = 10V, V_{DS} = 30V,$
Gate-Source Charge	Q _{gs}	_	0.1	_	nc	I _D = 150mA
Gate-Drain Charge	Q _{gd}		0.2			
Turn-On Delay Time	t _{D(ON)}	_	2.3	_		
Turn-On Rise Time	t _R		3.9			V _{DD} = 30V, I _D = 0.115A, V _{GEN} = 10V.
Turn-Off Delay Time	t _{D(OFF)}		11.4		ns	$R_{GEN} = 25\Omega$
Turn-Off Fall Time	t _F		16.7			

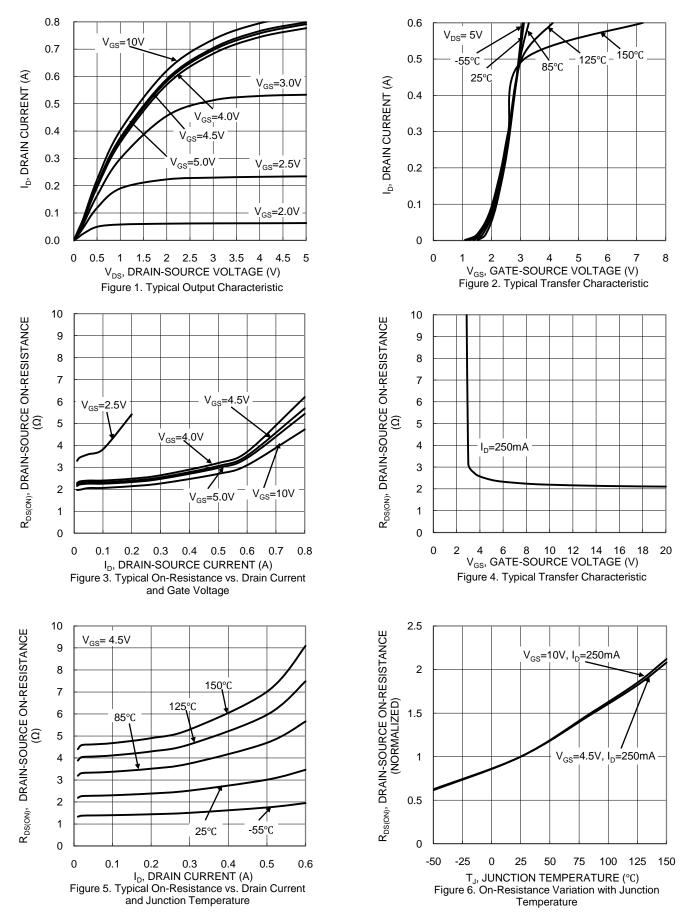
5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

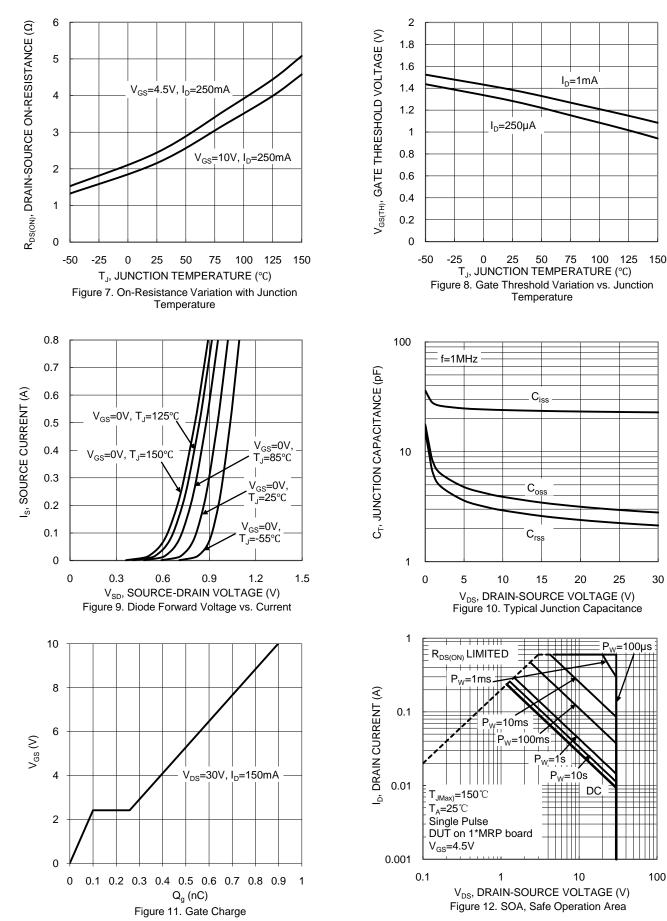


DMN63D8L



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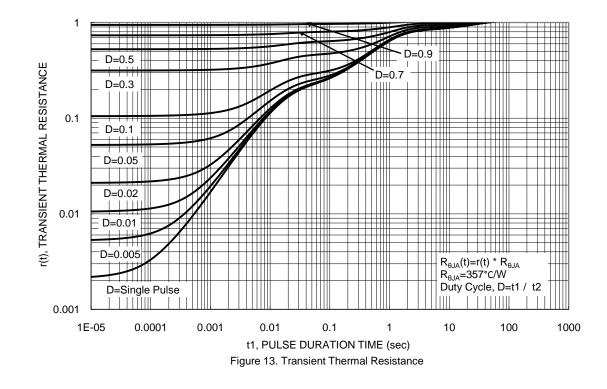
NEW PRODUCT

DMN63D8L Document number: DS38026 Rev. 1 - 2

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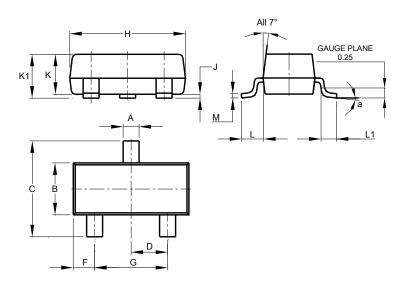
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Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

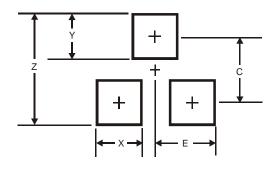


	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
К	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
М	0.085	0.150	0.110						
а		8°							
All	Dimens	ions in	mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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